

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

~~The present invention provides an~~ An underlayer film-forming material for copper, a method for forming the underlayer, an underlayer film for copper, and a semiconductor device including a substrate, the underlayer and copper wiring film, which ~~enable the prevention of~~ prevents copper diffusion as well as ~~provide~~ provides superior adhesion to a copper wiring film, even if the film is thinner than conventional barrier metals. The underlayer film-forming material for copper ~~includes~~ is formed from a compound represented by a ~~following general formula [I]:~~  $(R_1R_2)P-(R)_n-Si(X_1X_2X_3)$ , wherein at least one of  $X_1$ ,  $X_2$ , and  $X_3$  represents a hydrolysable group; each of  $R_1$  and  $R_2$  represents an alkyl group;  $R$  represents a divalent linear organic group which is ~~formed of~~ selected from an alkylene group, an aromatic ring, ~~or~~ and an alkylene group including an aromatic ring; and  $n$  ~~represents~~ is an integer ~~of~~ from 1 to 6.